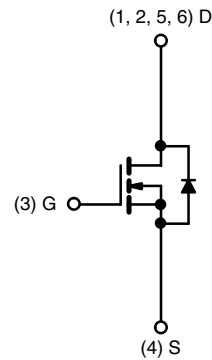
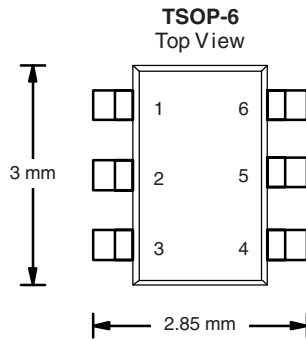


## N-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
20	0.057 at $V_{GS} = 4.5$ V	4.2
	0.090 at $V_{GS} = 2.5$ V	3.4



**RoHS**  
COMPLIANT



**Ordering Information:** Si3442BDV-T1-E3 (Lead (Pb)-free)

**Marking Code:** 2Bxxx

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	20		V	
Gate-Source Voltage	$V_{GS}$	$\pm 12$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	4.2	3.0	A
		$T_A = 70$ °C	3.4	2.4	
Pulsed Drain Current	$I_{DM}$	20			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	1.4	0.72	W	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	1.67		0.86
		$T_A = 70$ °C	1.07		0.55
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 5$ s	75	100	°C/W
		Steady State	120	145	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	70	85		

Notes:

a. Surface Mounted on FR4 Board,  $t \leq 5$  s.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>.



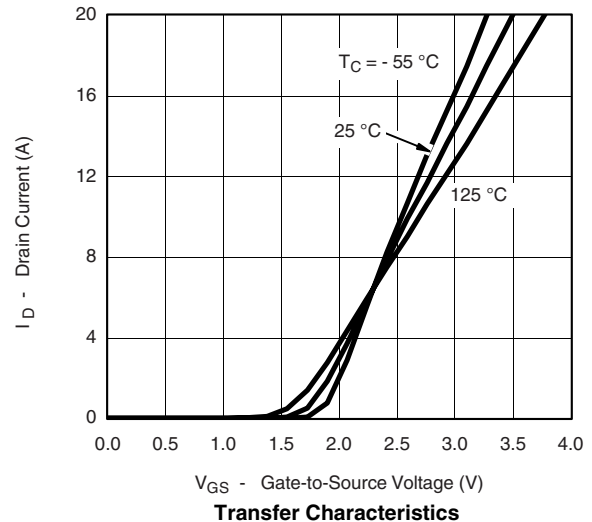
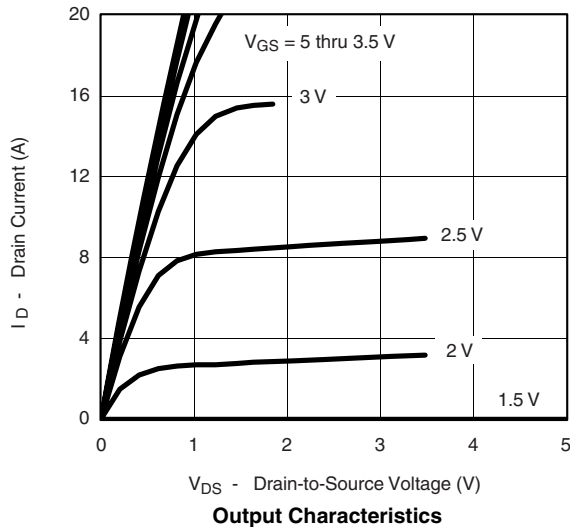
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6		1.8	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 4.5\text{ V}$	10			A
		$V_{DS} = 5\text{ V}, V_{GS} = 2.5\text{ V}$	4			
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 4\text{ A}$		0.045	0.057	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 3.4\text{ A}$		0.070	0.090	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 4.0\text{ A}$		11.3		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.6\text{ A}, V_{GS} = 0\text{ V}$		0.75	1.2	V
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		295		pF
Output Capacitance	$C_{oss}$			75		
Reverse Transfer Capacitance	$C_{rss}$			45		
Total Gate Charge	$Q_g$	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 4.0\text{ A}$		3	5	nC
Gate-Source Charge	$Q_{gs}$			0.65		
Gate-Drain Charge	$Q_{gd}$			0.95		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		2.7		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$		35	55	ns
Rise Time	$t_r$			50	75	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	$t_f$			15	25	
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = 1.6\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	

Notes:

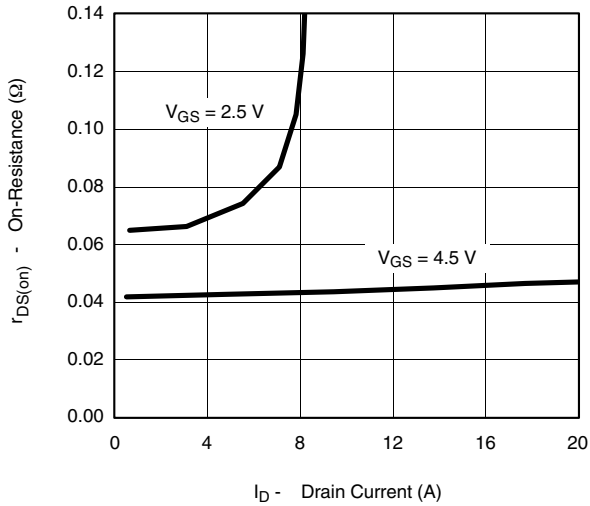
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

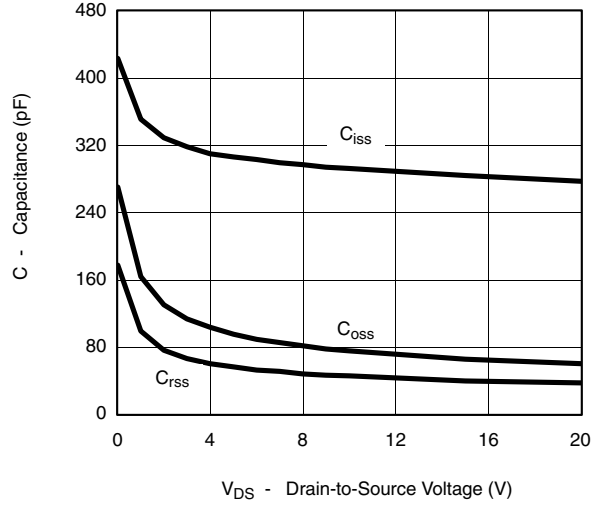
**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted



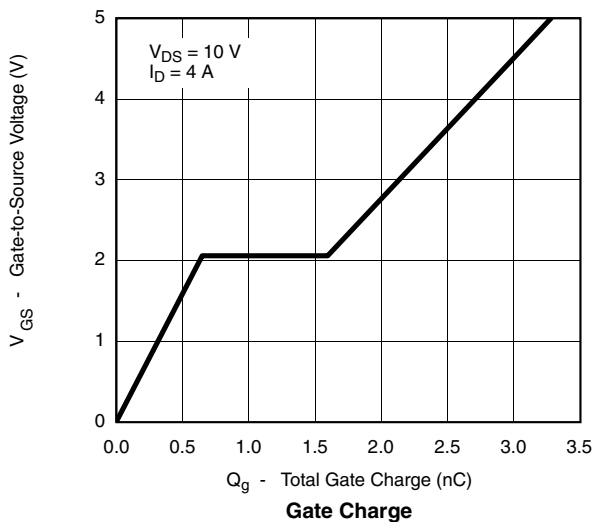
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



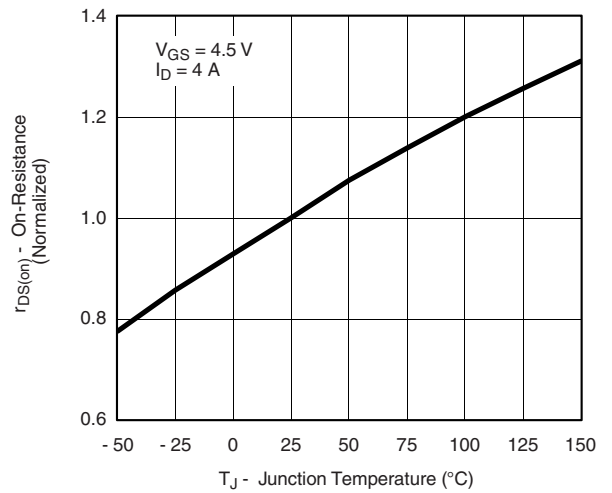
**On-Resistance vs. Drain Current**



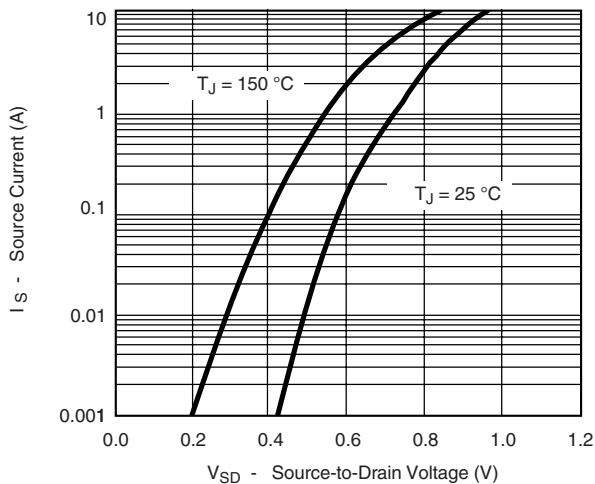
**Capacitance**



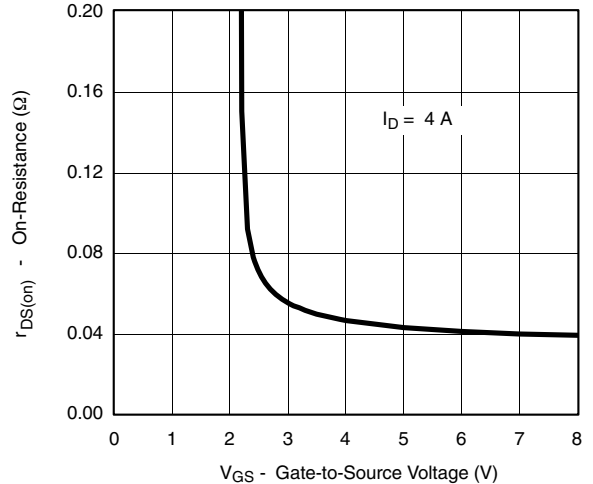
**Gate Charge**



**On-Resistance vs. Junction Temperature**

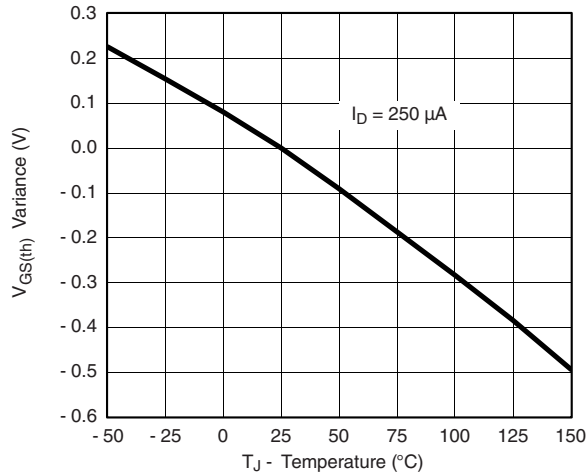


**Source-Drain Diode Forward Voltage**

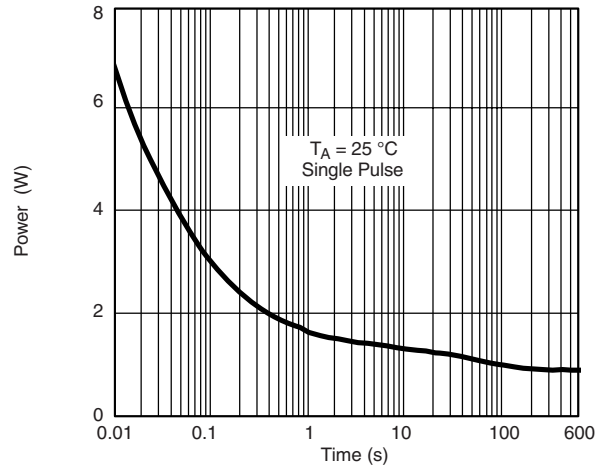


**On-Resistance vs. Gate-to-Source Voltage**

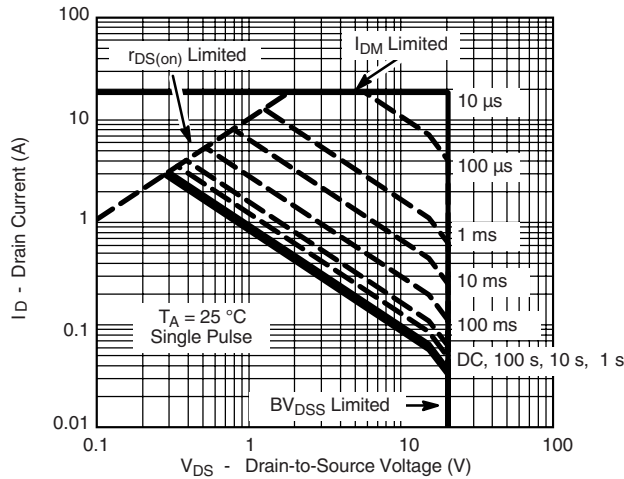
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



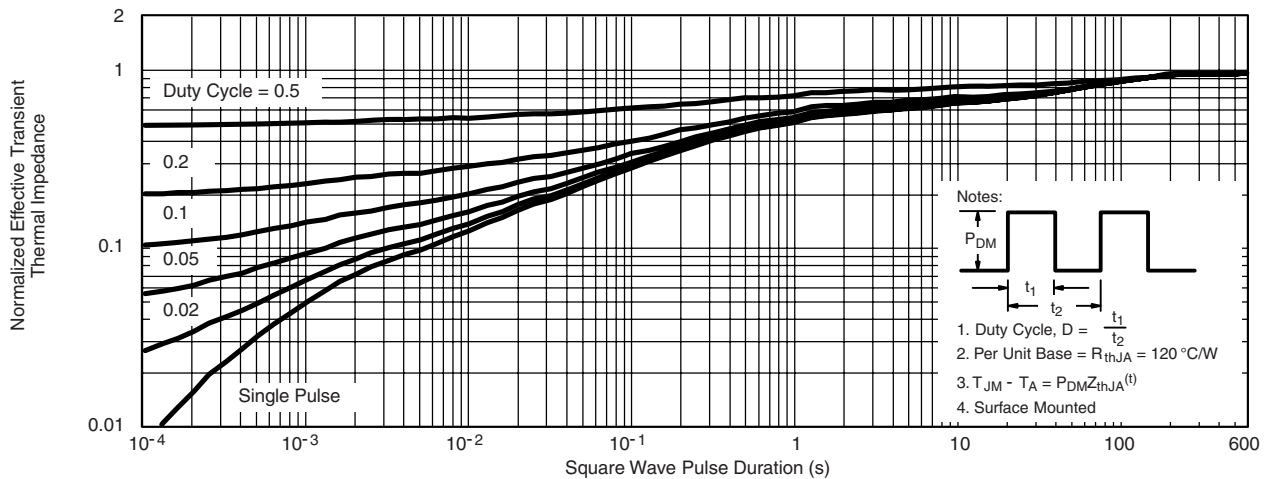
**Threshold Voltage**



**Single Pulse Power**



**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72504>.



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